

print out

Application serial number 200405408 (I289929)

Title Semiconductor memory device and method of manufacturing the same

Publication Date 2004/04/01 (2007/11/11)

Application Date 2003/08/29

Application No. 092124136

IPC H01L-021/00

Inventor KOMORI, HIDEKIJP;
SHIMADA, HISAYUKIJP;
SUN, YUUS;
KINOSHITA, HIROYUKIJP

Applicant FUJITSU LIMITEDJP;
FASL LLCUS;
ADVANCED MICRO DEVICES, INC.US

Priority Number 2002/08/30 JP20020256120

Abstract A semiconductor memory device and a method of manufacturing the same are disclosed, wherein a drain (7) has a low concentration and shallow low concentration impurity area (7a), which is formed in conformity with a control gate (5), and a high concentration impurity area (7b), which has higher concentration and is deeper than the low concentration impurity area (7a) and is formed in conformity with a side wall film (8). As a result, the short channel effect is improved and the programming efficiency is enhanced due to the low concentration impurity area (7a), and the contact resistance within the drain (7) is decreased while providing a drain contact hole forming portion (70) upon the high concentration impurity area (7b).

**Patent Right
Change**

Application number	092124136
Authorization note	No
Qualification right note	No
Transfer Note	No
Inheritance Note	No
Trust note	No
Objection note	No
Exposure Note	No
Invalidation date	
Withdrawal date	
Issue date of patent right	20071111
Due date of patent right	20230828
Due date of annual fee	20081110
Due year of annual fee	001